P-Channel 30 V (D-S) MOSFET

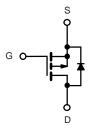
PRODUCT SUMMARY Q_g (Typ.) V_{DS} (V) $R_{DS(on)}(m\Omega)(Typ.)$ $I_D(A)^a$ 11 at V_{GS} = - 10 V- 30 - 21 14 nC 15.5 at V_{GS} = - 4.5 V

FEATURES

- DT-Trench Power MOSFET
- · Low Thermal Resistance
- Low Rds(ON) To Minimize Conductive Loss
- · Low Gate Charge For Fast Switching
- 100% Avalanche Tested

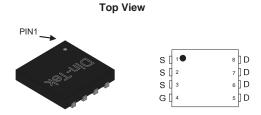
APPLICATIONS

- · POL Applications
- MB/VGA Vcore
- · BLDC Motor driver
- SMPS 2nd Synchronous Rectifier



P-Channel MOSFET

PDFN3.3X3.3-8L Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _J = 150° C) ^a	T _C = 25 °C	- I _D	- 21	А	
	T _C = 100 °C		- 12.6		
Pulsed Drain Current ^b		I _{DM}	- 84		
Single Avalanche Energy		E _{AS}	110	mJ	
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	30	W	
	T _C = 100 °C		12		
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	- 55 to + 150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R_{thJA}	62	°C/W		
Junction-to-Case (Drain)	R _{thJC}	4.2	C/VV		

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.2	-	- 2.2		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	=	-	± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V	-	-	- 1 μA		
		V _{DS} = - 24 V, V _{GS} = 0 V, T _J = 55 °C	=	-	- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge$ - 5 V, $V_{GS} =$ - 10 V	- 21	-	-	Α	
Drain-Source On-State Resistance ^a	D-a	V _{GS} = - 10 V, I _D = - 10 A	-	11	16	m0	
Diam-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 6 A	-	15.5	21	mΩ	
Forward Transconductance ^a	9fs	V _{DS} = - 5 V, I _D = - 6 A	-	8	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	1350	-	pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = - 15 V, f = 1 MHz	-	194	-		
Reverse Transfer Capacitance	C _{rss}		-	158	-		
Total Gate Charge ^c	Q_g		-	14	-	nC	
Gate-Source Charge ^c	Q _{gs}	V _{DS} = - 25 V, V _{GS} = - 10 V, I _D = - 15 A	-	5.2	-		
Gate-Drain Charge ^c	Q_{gd}		-	5.0	-		
Gate Resistance	R _g	f = 1 MHz	-	14	-	Ω	
Turn-On Delay Time c	t _{d(on)}		-	10.5	-		
Rise Time ^c	t _r	$V_{DD} = -25 \text{ V}, R_{q} = 3.3 \Omega,$	-	11	-		
Turn-Off Delay Time ^c	t _{d(off)}	R _L = 0.75 A , Vgs = - 10 V	-	51	-	ns	
Fall Time ^c	t _f		-	28	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	- 21	Α	
Pulsed Current	I _{SM}		-	-	- 84	Α	
Forward Voltage ^a	V_{SD}	I _F = - 10 A, V _{GS} = 0 V	-	-	-1.2	V	
Reverse Recovery Time	t _{rr}	0.4 11/11 500.4/	-	14	-	ns	
Reverse Recovery Charge	Q _{rr}	I _F = - 9 A, di/dt = 500 A/μs	-	35	_	nC	

Notes

- a. Pulse test; pulse width ≤ 200 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

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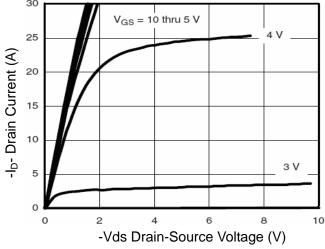


Figure 1 Output Characteristics

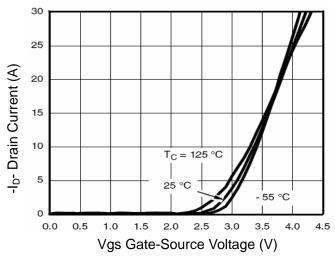


Figure 2 Transfer Characteristics

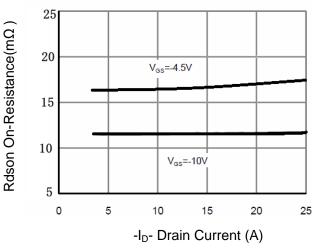


Figure 3 Rdson- Drain Current

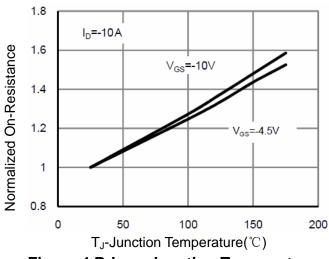


Figure 4 Rdson-Junction Temperature

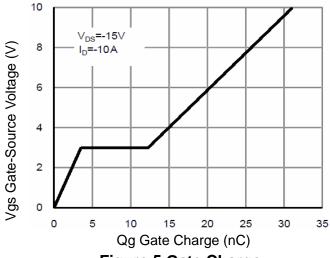


Figure 5 Gate Charge

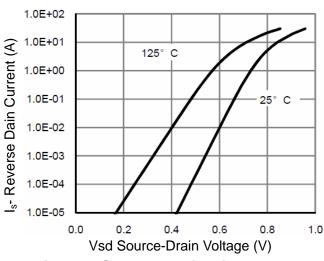


Figure 6 Source- Drain Diode Forward



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

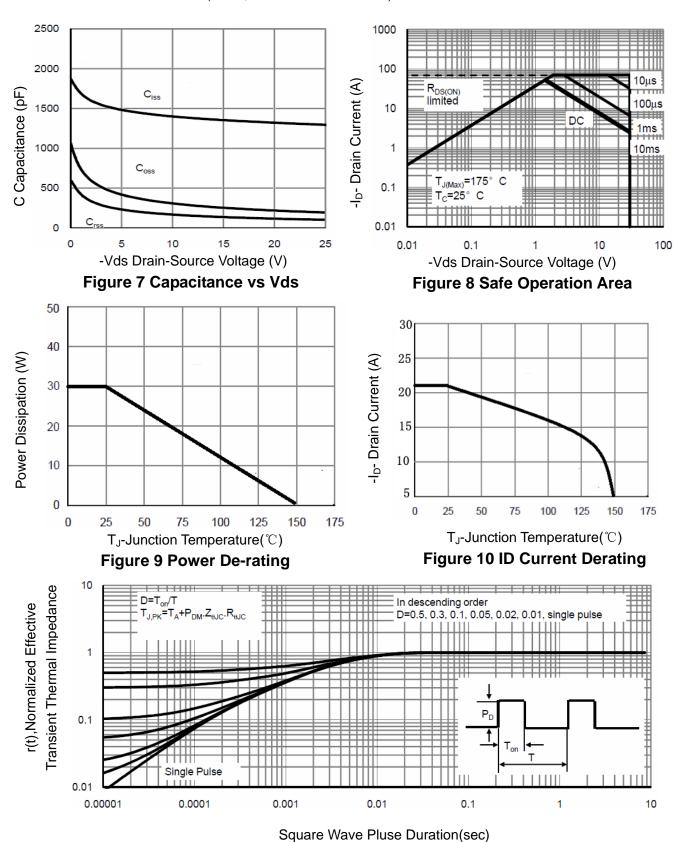
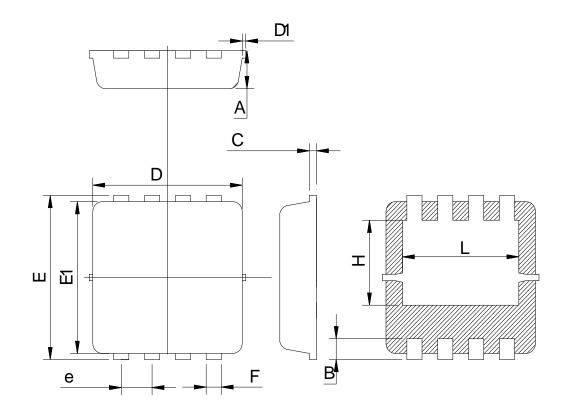


Figure 11 Normalized Maximum Transient Thermal Impedance



PDFN 3.3X3.3-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
А	0.600	0.775	1.000
В	0.20	0.38	0.55
С	0.05	0.15	0.40
D	3.10	3.25	3.50
D1	-	-	0.15
Е	3.15	3.35	3.50
E1	2.60	3.10	3.45
е	0.50	0.65	0.80
F	0.15	0.32	0.45
Н	1.25	1.73	2.10
L	2.20	2.45	2.85





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